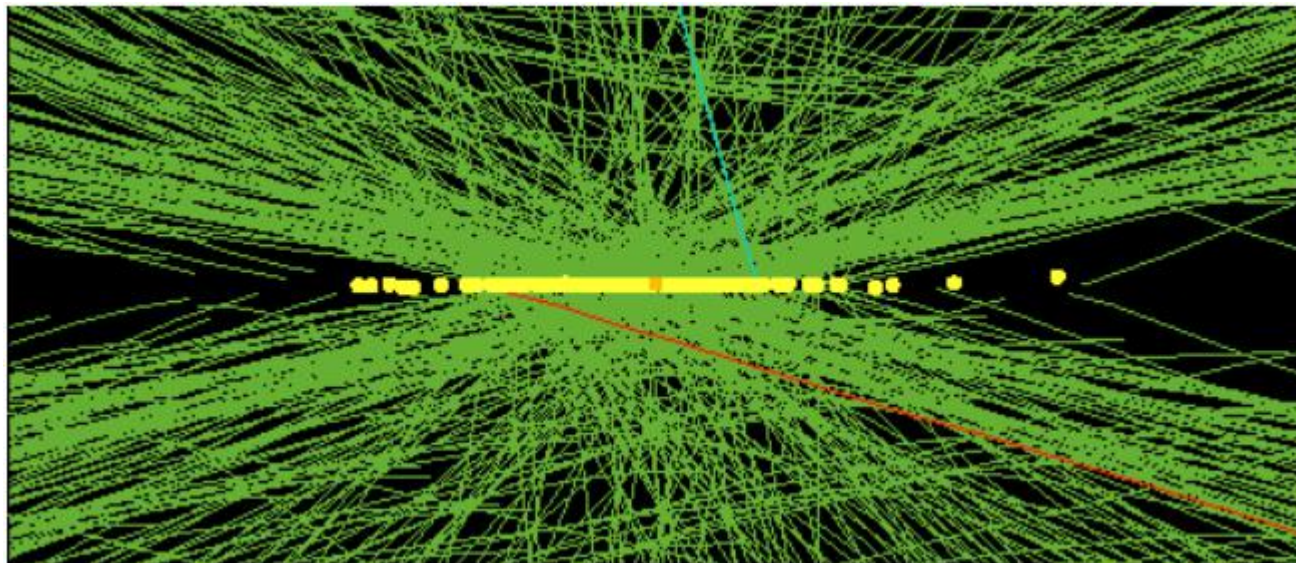


# **Low-Gain Avalanche Detector for 4D Tracking**

Suyu XIAO from IHEP

2008-09-14

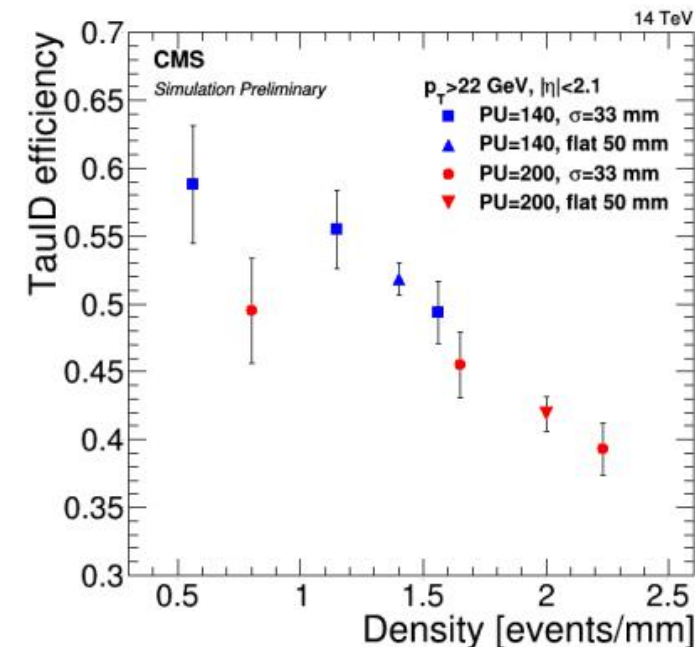
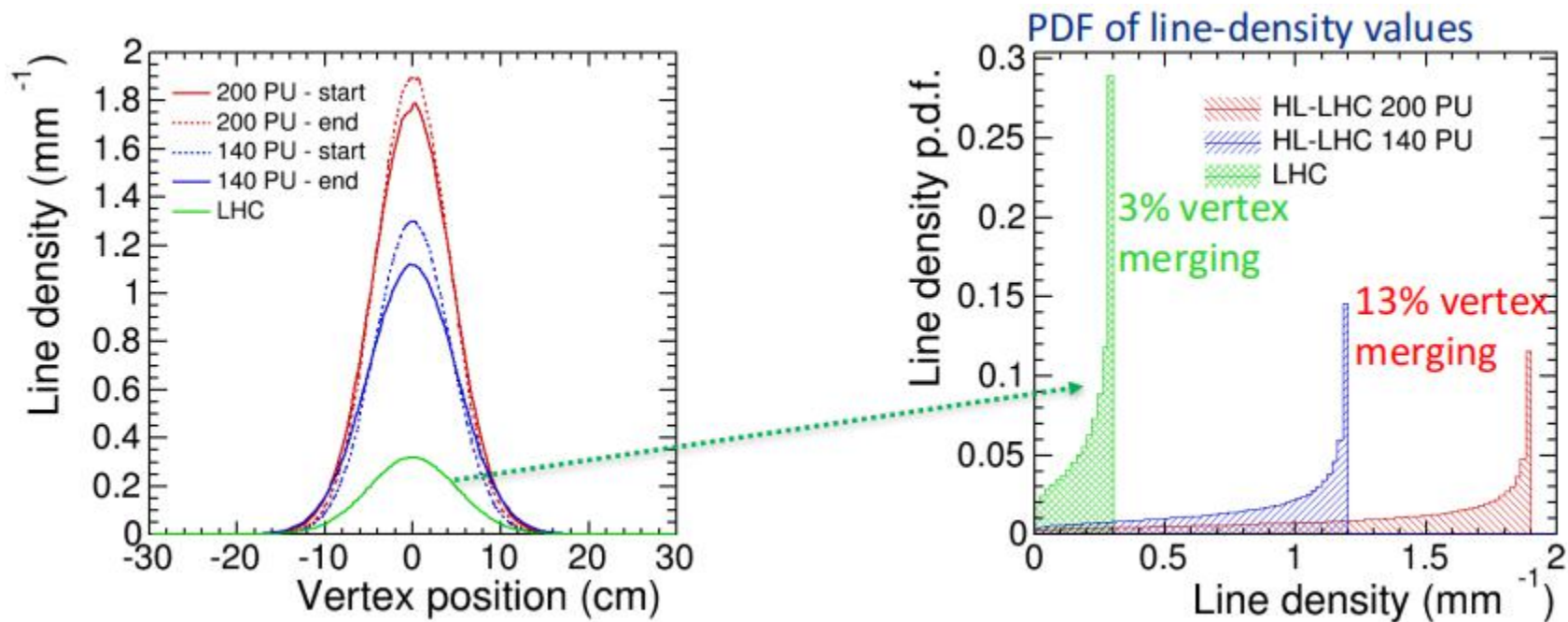
# Why 4D Tracking?



- HL-LHC environment:
  - Pileup up to 200 (180ps, 50mm)
  - Additional energy, extra jets, reducing the performance of several physics objects and particularly important for trigger
- Extended tracking coverage up to  $|\eta| = 4.0$ 
  - Main handle against pileup
  - 5-7 vertices within tracker resolution at large  $|\eta|$  (only 1/3 of the effect in the central region)

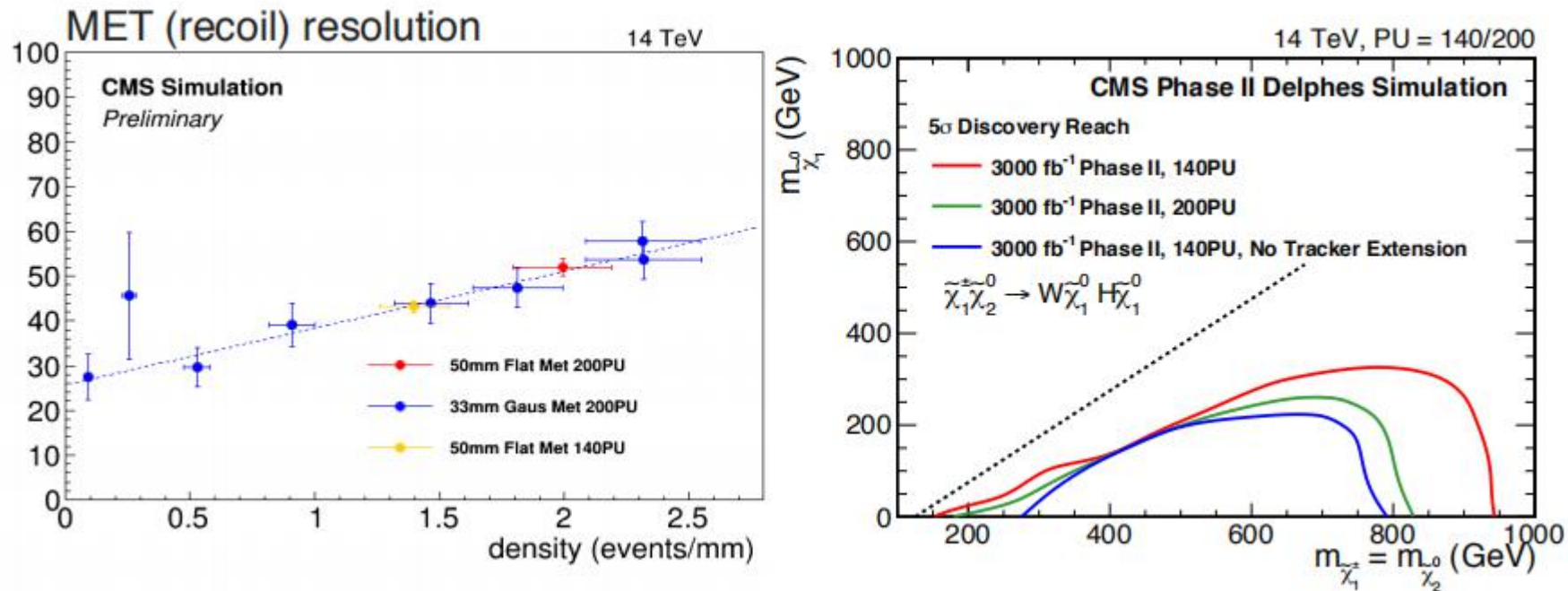
# Effects of High Pileup in Reconstruction

- HL-LHC sees a substantial increase in the peak pileup line-density
- Large rate 'merged' vertices even after upgrades



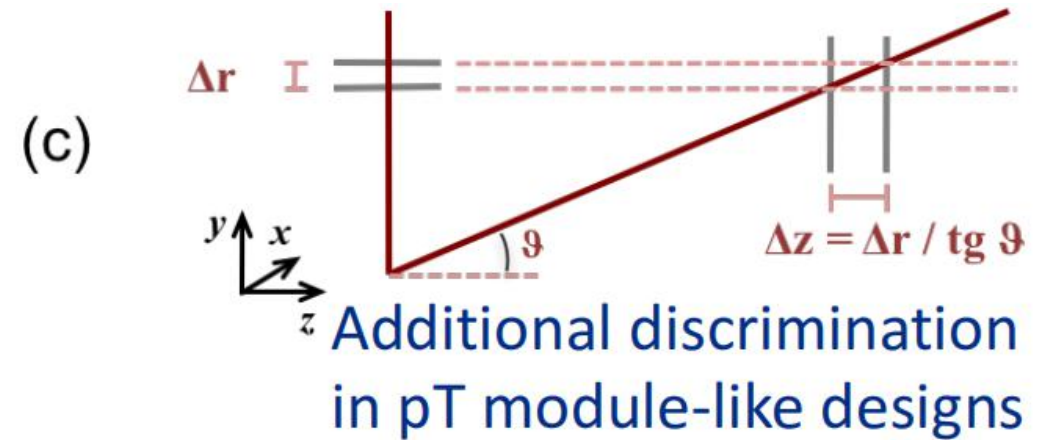
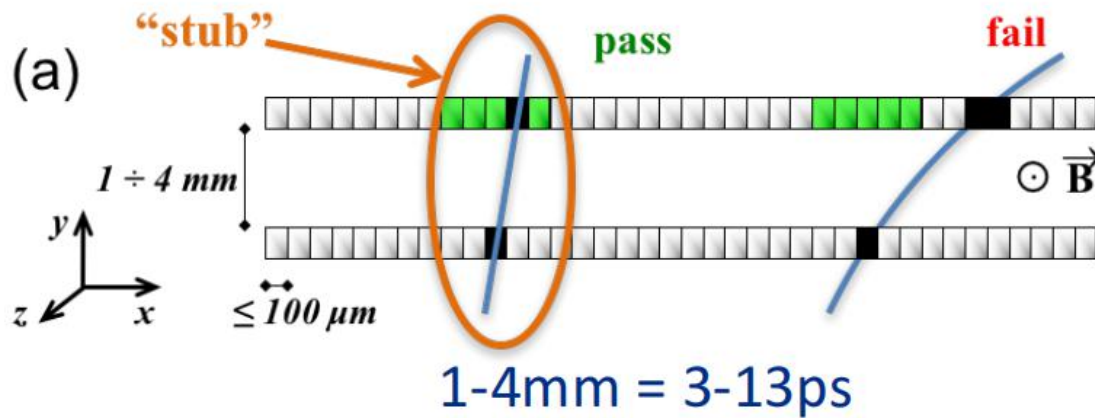
# Effects of High Pileup in Analysis

- These reconstruction and physics object impacts percolate to the analysis level



# Algorithmic Effects in 4D Tracking

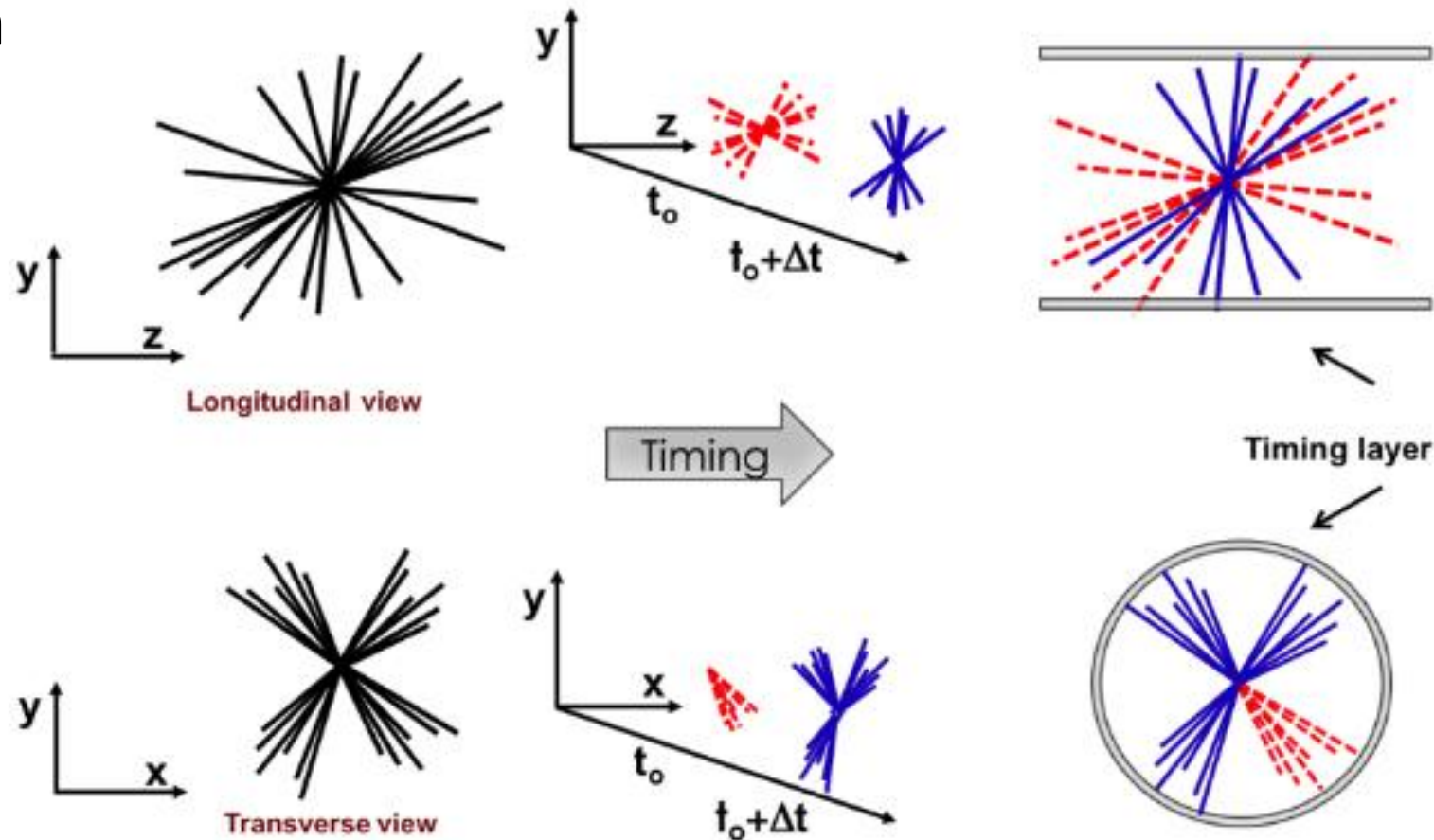
- Combinatorial reduction from more clean track seeds
- Could put timing into pT modules to remove fake stubs adding time coincidence cut





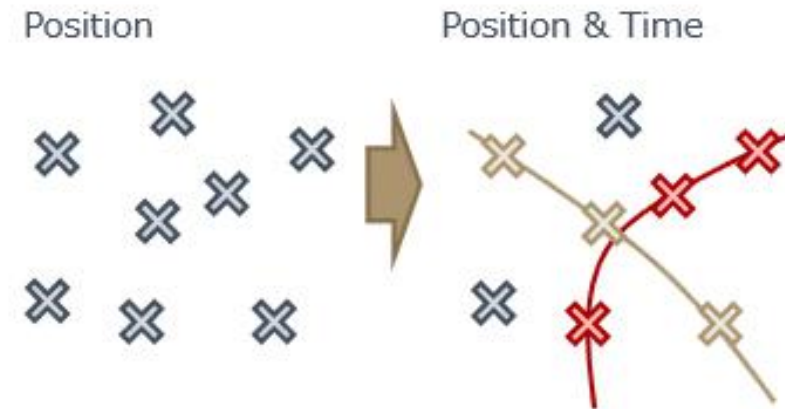
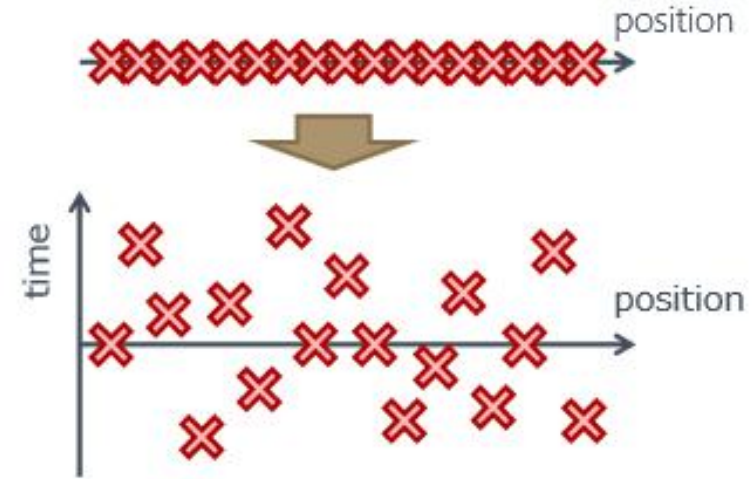
# Timing in Event Reconstruction

- Timing allows distinguishing overlapping events by means of an extra dimension



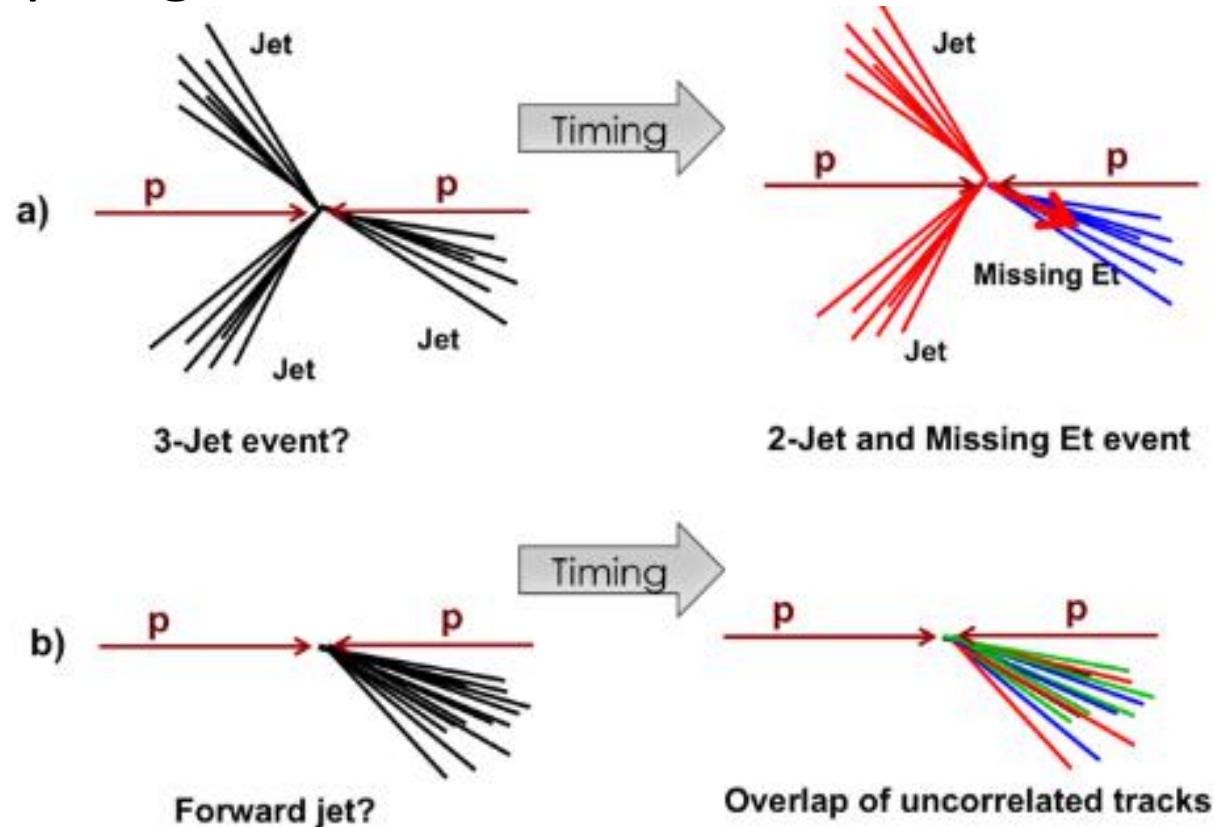
# Timing in Track Reconstruction

- Massive simplification of pattern recognition, new tracking algorithms will be faster even in very dense environments
- Use only time compatible points



# Timing at Trigger Level

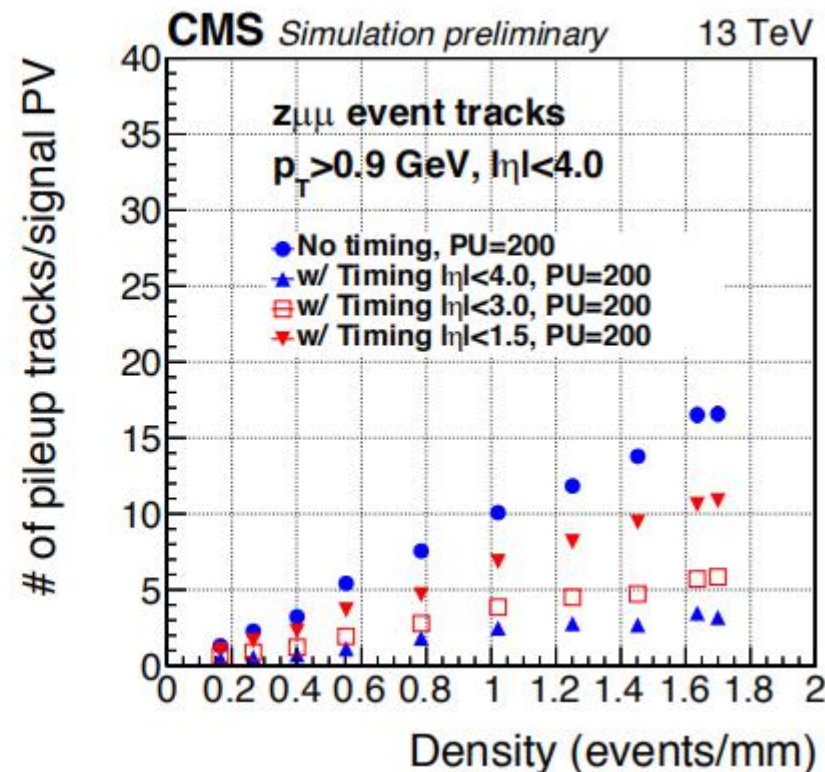
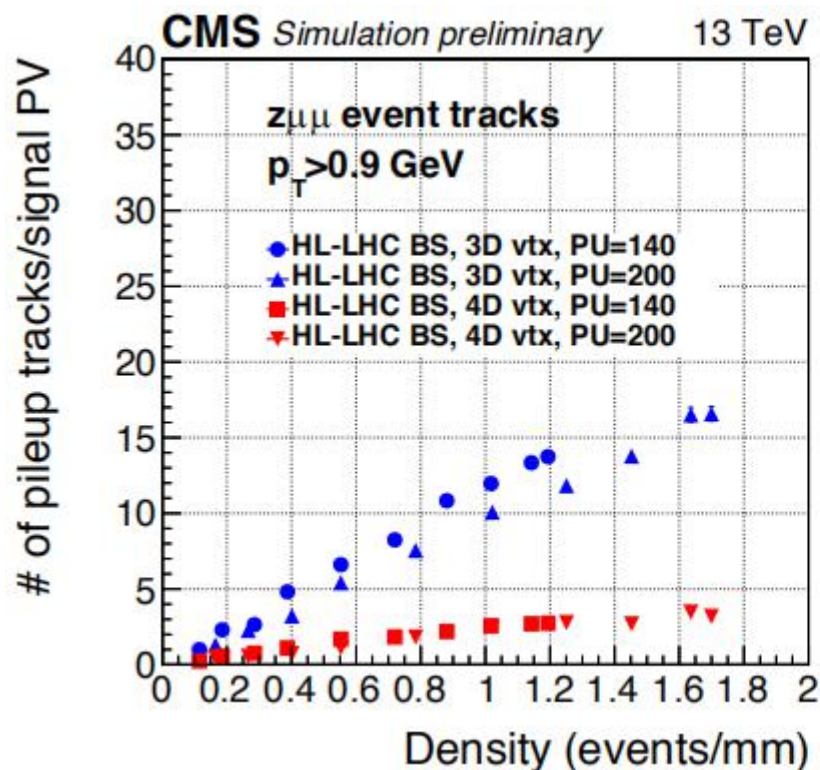
- Timing at the trigger decision allows reducing the trigger rate rejecting topologies that look similar





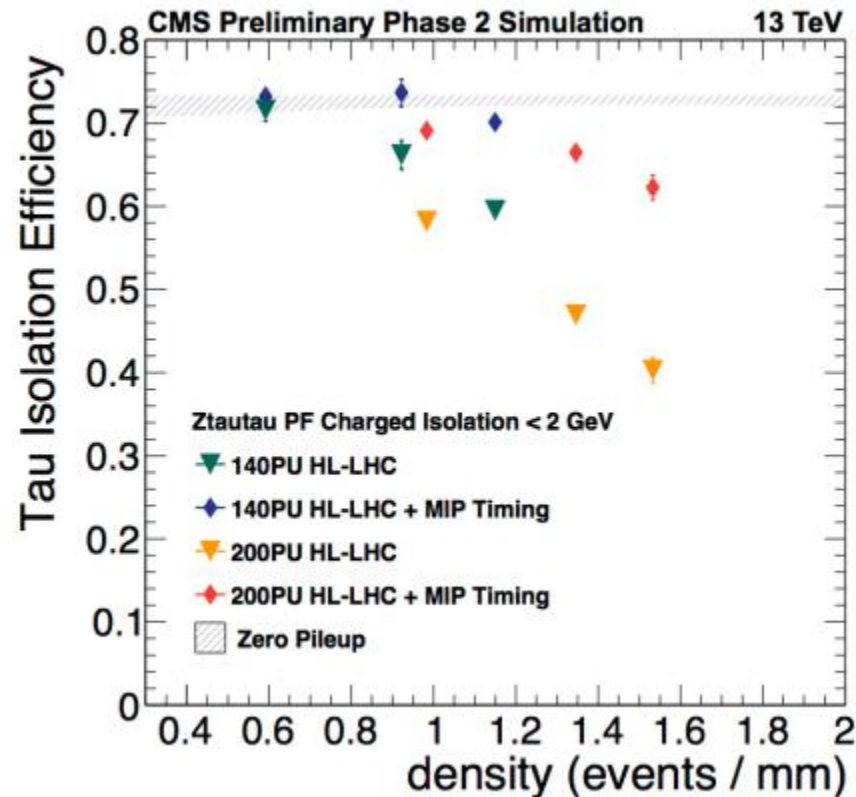
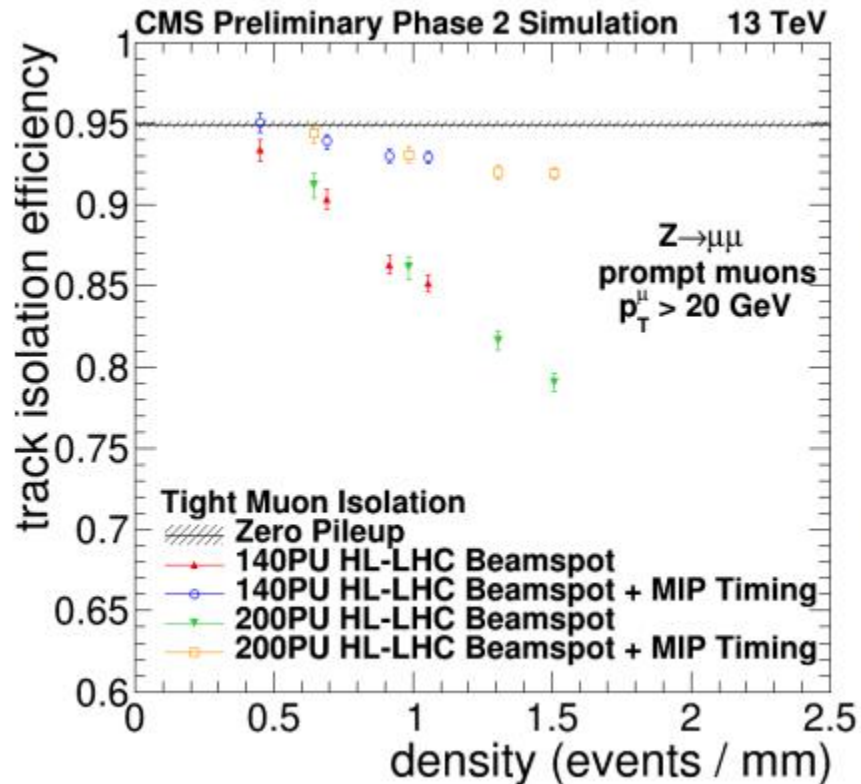
# Effects of Timing on Track-Vertex Association

- Large improvement assuming a hermetic timing layer, total improvement scales with solid angle that is covered by the detector



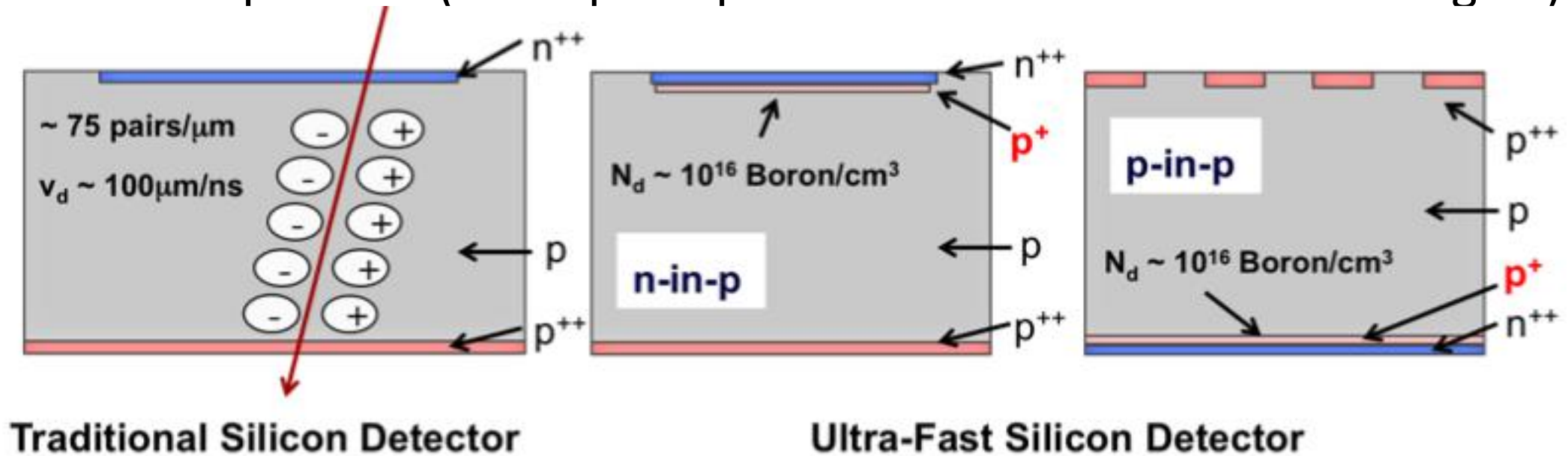
# Impact of Track Timing at the Analysis Level

- There is a significant improvement in the efficiency.



# LGAD - Ultra-Fast Silicon Detector

- Adding a highly doped, thin layer of p-implant near the p-n junction creates a high electric field that accelerates the electrons enough to start multiplication (same principle of APD but with much lower gain)



# LGAD - Ultra-Fast Silicon Detector

- Why low gain?
  - Milder electric fields, possible electrodes segmentation, lower shot noise, no dark count, behaviour similar to standart Silicon sensors
- Why thin sensors?
  - Highe signal steepness, more radiation resistance, easier to achieve parallel plate geometry, smaller Landau Noise

# Sensor

## Silicon Sensors

- ▷ GigaTracker NA62:  $\sigma_t \sim 150$  ps
- ▷ Silicon detector + SiGe HBT amplifier<sup>[1]</sup>:  $\sigma_t \sim 105$  ps
- + Fine segmentation easy
- + Known technology
- Small signal
- ✦ Intrinsic resolution:  $\sigma_t \sim 100$  ps

## Diamond Detectors

- ▷ TOTEM Diamonds for CT-PPS ToF:  $\sigma_t \sim 100$  ps
- + No leakage current
- + Radiation hard
- + Small capacitance, high mobility
- Small signal
- ✦ Intrinsic resolution:  $\sigma_t \sim 100$  ps

## APD (Avalanche PhotoDiodes)

- + Thin sensors (30-50  $\mu\text{m}$ )
- + High signal (gain 50-500)
- Sensitive to shot noise
- Radiation resistance up to  $10^{14} n_{\text{eq}}/\text{cm}^2$
- Fine segmentation difficult
- ✦ Intrinsic resolution:  $\sigma_t \sim 30$  ps

## LGAD (Low Gain Avalanche Diodes)

- + Thin sensors (50  $\mu\text{m}$ )
- + Medium-high signal (gain 10-20)
- + Shot noise under control
- Radiation resistance under investigation (within RD50 Coll.)
- Possible fine segmentation
- ✦ Intrinsic resolution:  $\sigma_t \sim 30$  ps



# LGAD - Ultra-Fast Silicon Detector

$$\sigma_{tot}^2 = \sigma_{Landau}^2 + \left( \frac{t_{rise}}{S/N} \right)^2 + \left( \left[ \frac{V_{thr}}{S/t_{rise}} \right]_{RMS} \right)^2 + \left( \frac{TDC_{bin}}{\sqrt{12}} \right)^2$$

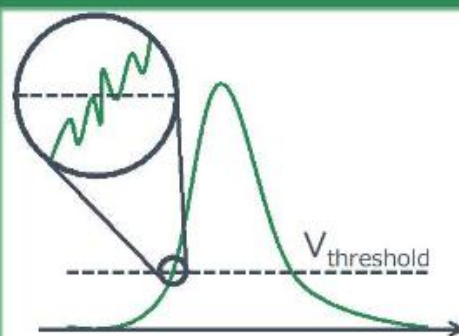
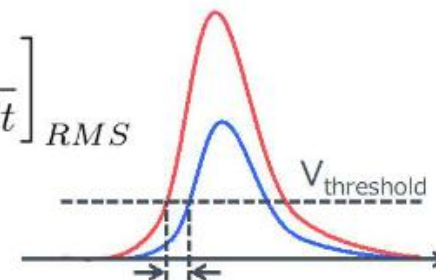
thin sensor  
(50  $\mu\text{m}$ )

fast signals  
large S/N

timewalk correction with CFD  
small TDC bins

$$\sigma_{det}^2 = \sigma_{Landau}^2 + \sigma_{TimeWalk}^2 + \sigma_{Jitter}^2$$

$$\sigma_{TimeWalk} = \left[ \frac{V_{th}}{S/t_{rise}} \right]_{RMS} \propto \left[ \frac{N}{dV/dt} \right]_{RMS}$$



$$\sigma_{Jitter} = \frac{N}{(dV/dt)} \simeq \frac{t_{rise}}{(S/N)}$$

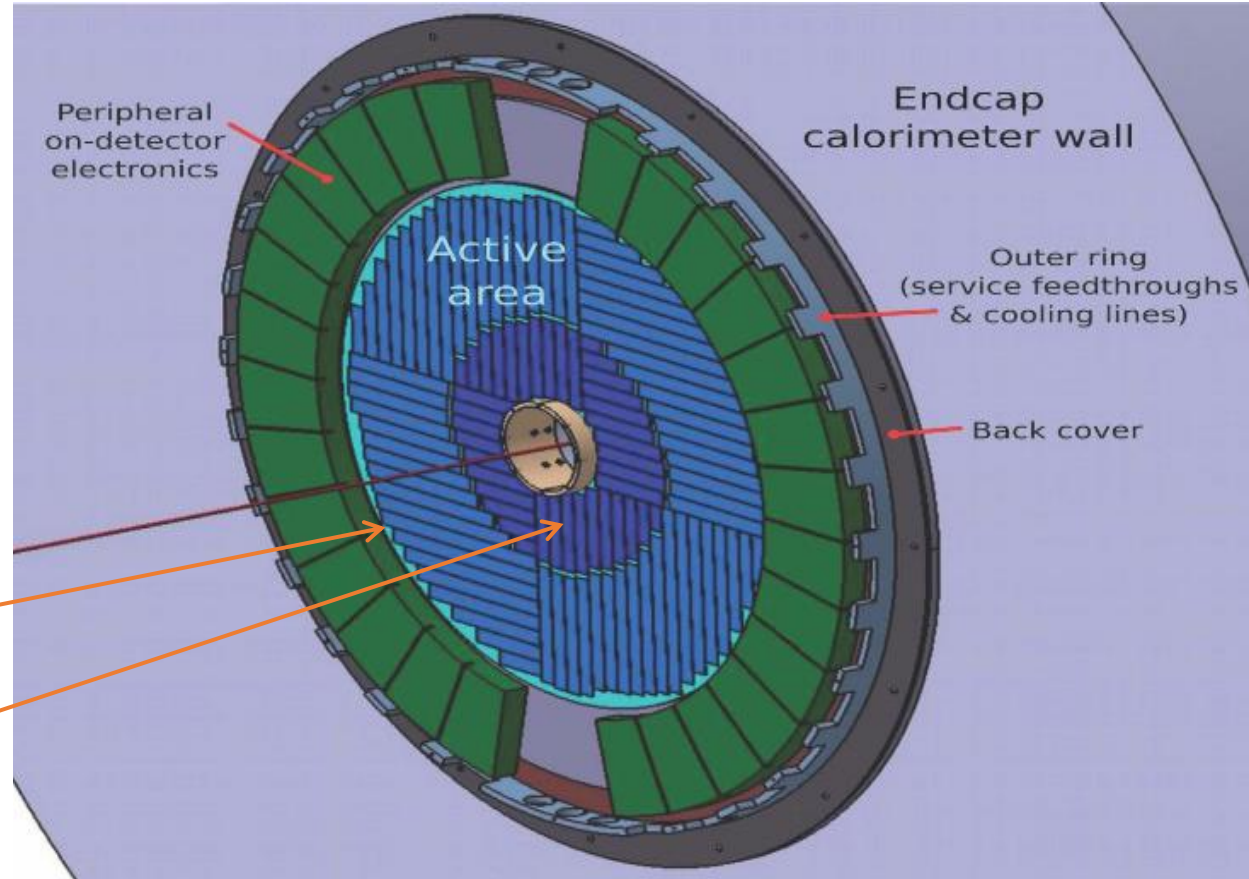
# High-Granularity Timing Detector

- Design & Requirements

- $z = 3420\text{-}3545\text{mm}$  ( $3435\text{-}3485\text{mm}$ )
- $2.4 < |\eta| < 4.0$  (forward region)
- $R = 110 - 1100\text{mm}$  ( $120 - 640\text{mm}$ )
- Time resolution:  $30\text{ps}/\text{track}$
- Pad size:  $1.3 * 1.3 \text{ mm}^2$

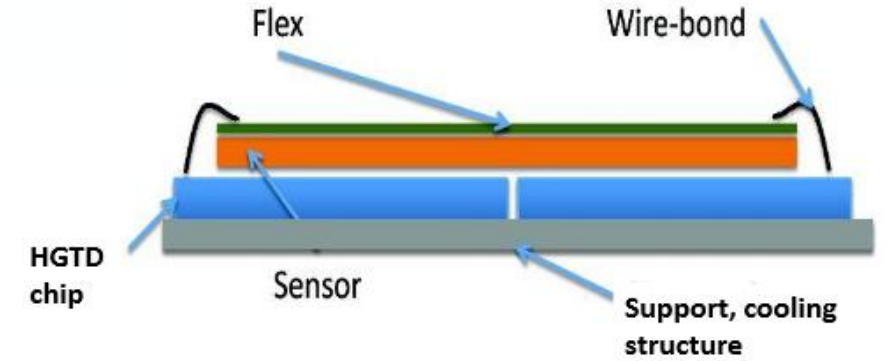
luminosity monitor

planned to be  
replaced once

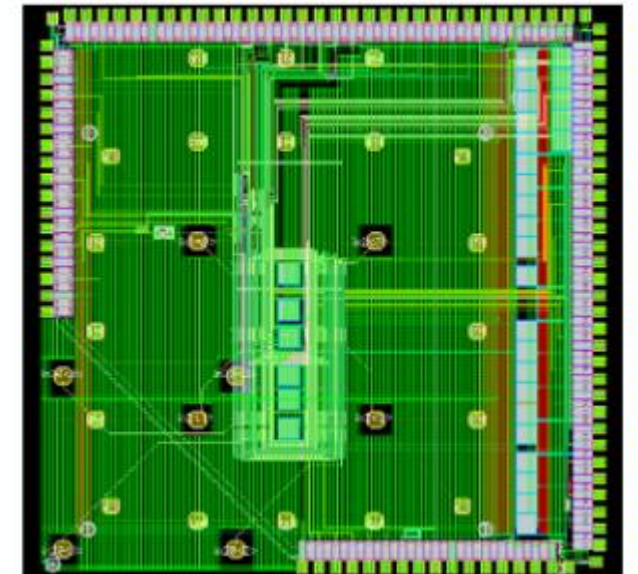


# HGTD Preliminary Design

- 2\*2 array of sensors bump-bonded to ASICs
- Flex used for readout signal and voltage distribution
- Modules staggered to minimise dead areas
- 1\*1mm<sup>2</sup> pads everywhere

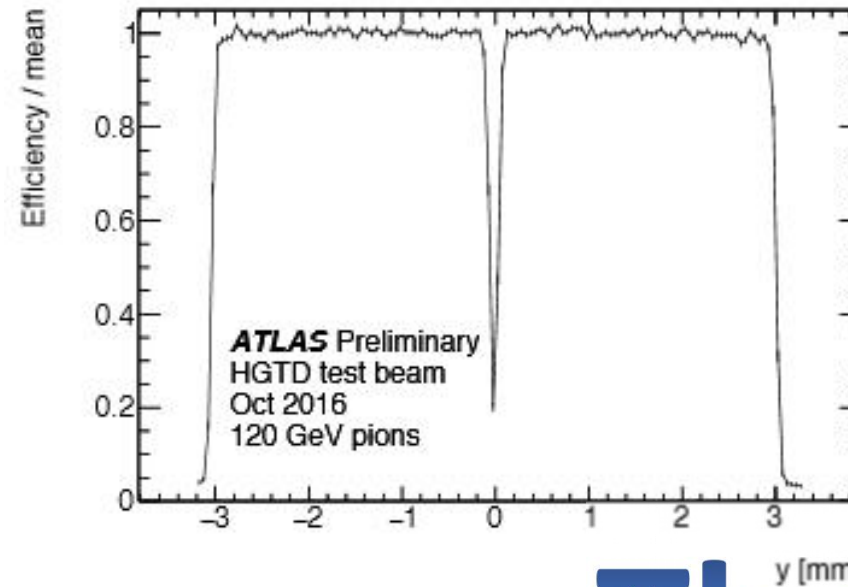
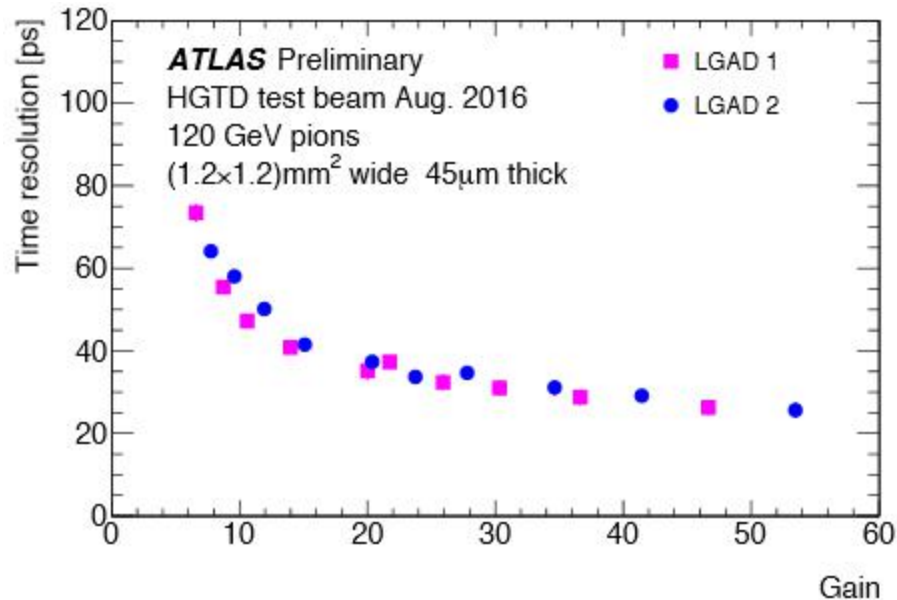


Chip layout with wire bonds in the periphery



# Test-beam Results

- Gains up to 50, time resolution  $< 30\text{ps}$  for  $1 \times 1\text{ mm}^2$  pads, dominated by Landau fluctuations
- Good efficiency and signal uniformity for arrays



Thanks!